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Sheet		1	of		1
		Application Number		10/743,906	
		Filing Date		12/24/2003	
		First Named Inventor		Ryu OGIWARA et al.	
		Group Art Unit		2824	
		Examiner Name		Unknown	
		Attorney Docket Number		001701.00198	

U.S. PATENT DOCUMENTS						
Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Examiner Signature		Date Considered	01/13/2006
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